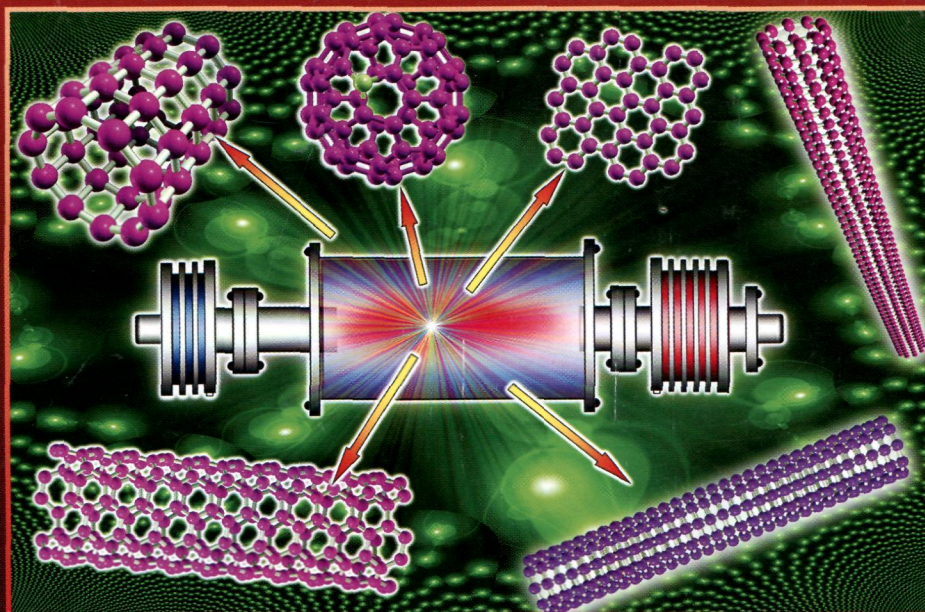


# JVST B

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## Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena



*Image credit: Igor Levchenko, Michael Keidar, Shuyan Xu, Holger Kersten, and Kostya (Ken) Ostrikov, JVST B, 31(5), p. 050801-1*

**Review Article:**  
**Low-temperature plasmas in carbon nanostructure synthesis**  
*-by Igor Levchenko, Michael Keidar, Shuyan Xu, Holger Kersten, and Kostya (Ken) Ostrikov*



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### Letters

<b>Vacuum frequency mixer with a field emitter array</b> Yasuhito Gotoh, Yoshiki Yasutomo, and Hiroshi Tsuji .....	050601
<b>Flexible substrate and release layer for flexible MEMS devices</b> Moinuddin Ahmed and Donald P. Butler .....	050602
<b>Organic-inorganic hybrid gate dielectric for solution-processed ZnO thin film transistors</b> Ji-Young Oh, Sang-Chul Lim, Joo Yeon Kim, Chul Am Kim, Kyoung-Ik Cho, Seong Deok Ahn, Jae Bon Koo, and Sung-Min Yoon .....	050603
<b>Influence of porosity on dielectric breakdown of ultralow-<i>k</i> dielectrics</b> Kris Vanstreels, Ivan Ciofi, Yohan Barbarin, and Mikhail Baklanov .....	050604
<b>Effects of operational and geometrical conditions upon photosensitivity of amorphous InZnO thin film transistors</b> Sungho Park, Sekyoung Park, Seung-Eon Ahn, Ihun Song, Wonseok Chae, Manso Han, Jeseung Lee, and Sanghun Jeon .....	050605
<b>Fabrication of transferrable, fully suspended silicon photonic crystal nanomembranes exhibiting vivid structural color and high-Q guided resonance</b> Chenxi Lin, Luis Javier Martínez, and Michelle L. Povinelli .....	050606
<b>Fabrication of GaN nanodots via GaN thermal decomposition in H<sub>2</sub> atmosphere</b> Xiong Hui, Jin Zhang, Senlin Li, Hu Wang, Yanyan Fang, Jiangnan Dai, and Changqing Chen .....	050607

(Continued)

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**Low-temperature plasmas in carbon nanostructure synthesis**

Igor Levchenko, Michael Keidar, Shuyan Xu, Holger Kersten, and Kostya (Ken) Ostrikov ..... 050801

**Electronic & Optoelectronic Materials, Devices & Processing****Empirical correlation for minority carrier lifetime to defect density profile in germanium on silicon grown by nanoscale interfacial engineering**

Josephine J. Sheng, Darin Leonhardt, Sang M. Han, Steven W. Johnston, Jeffrey G. Cederberg, and Malcolm S. Carroll ..... 051201

**Influence of the hydrogen implantation power density on ion cutting of Ge**

Yujiao Ruan, Wang Lin, Songyan Chen, Cheng Li, Hongkai Lai, Wei Huang, and Jun Li ..... 051202

**Thermal pretreatment of sapphire substrates prior to ZnO buffer layer growth**

Shimin Huang, Shulin Gu, Shunming Zhu, Ran Gu, Kun Tang, Jiandong Ye, Rong Zhang, Yi Shi, and Youdou Zheng ..... 051203

**Planar metal-insulator-metal diodes based on the Nb/Nb<sub>2</sub>O<sub>5</sub>/X material system**

Matthew L. Chin, Prakash Periasamy, Terrance P. O'Regan, Matin Amani, Cheng Tan, Ryan P. O'Hayre, Joseph J. Berry, Richard M. Osgood III, Philip A. Parilla, David S. Ginley, and Madan Dubey ..... 051204

**Determining local residual stresses from high resolution wafer geometry measurements**

Jie Gong, Pradeep Vukkadala, Jaydeep K. Sinha, and Kevin T. Turner ..... 051205

**Discrepancies in the nature of nitrogen incorporation in dilute-nitride GaSbN and GaAsN films**

Wendy L. Sarney and Stefan P. Svensson ..... 051206

**Low-damage silicon etching using a neutral beam**

Kazuhiro Miwa, Yuki Nishimori, Shinji Ueki, Masakazu Sugiyama, Tomohiro Kubota, and Seiji Samukawa ..... 051207

**Temperature stability of high-resistivity GaN buffer layers grown by metalorganic chemical vapor deposition**

Alexander Y. Polyakov, N. B. Smirnov, E. A. Kozhukhova, Andrei V. Osinsky, and Stephen J. Pearton ..... 051208

**Ohmic contacts fabricated on moderately doped p-type GaAs by sputtering deposition and a laser-firing process**

Alfredo Boronat, Santiago Silvestre, and Albert Orpella ..... 051209

**Electrical characterization of <sup>60</sup>Co gamma radiation-exposed InAlN/GaN high electron mobility transistors**

Hong-Yeol Kim, Jihyun Kim, Lu Liu, Chien-Fong Lo, Fan Ren, and Stephen J. Pearton ..... 051210

**Three-step growth of metamorphic GaAs on Si(001) by low-pressure metal organic chemical vapor deposition**

Yifan Wang, Qi Wang, Zhigang Jia, Xiaoyi Li, Can Deng, Xiaomin Ren, Shiwei Cai, and Yongqing Huang ..... 051211

**Highly thermally stable *in situ* SiN<sub>x</sub> passivation AlGaIn/GaN enhancement-mode high electron mobility transistors using TiW refractory gate structure**

Hsien-Chin Chiu, Chao-Hung Chen, Chih-Wei Yang, Hsuan-Ling Kao, Fan-Hsiu Huang, Sheng-Wen Peng, and Heng-Kuang Lin ..... 051212

**Thin film Ni-Si solid-state reactions: Phase formation sequence on amorphized Si**

Pierre Turcotte-Tremblay, Matthieu Guihard, Simon Gaudet, Martin Chicoine, Christian Lavoie, Patrick Desjardins, and François Schiettekatte ..... 051213

**Nanometer Science & Technology****Patterning of silicon nitride for CMOS gate spacer technology. I. Mechanisms involved in the silicon consumption in CH<sub>3</sub>F/O<sub>2</sub>/He high density plasmas**

Romuald Blanc, François Leverd, Thibaut David, and Olivier Joubert ..... 051801

**Universal three-dimensional nanofabrication for hard materials**

Kenji Yamazaki and Hiroshi Yamaguchi ..... 051802

(Continued)

<b>Growth and characterization of InAs quantum dots on InP nanowires with zinc blende structure</b>	
Xin Yan, Xia Zhang, Junshuai Li, Jiangong Cui, Sijia Wang, Shuyu Fan, Yongqing Huang, and Xiaomin Ren . . . .	051803
<b>Smooth MgO films grown on graphite and graphene by pulsed laser deposition</b>	
Sean C. Stuart, Edward Satchet, Andreas Sandin, Jon-Paul Maria, John E. (Jack) Rowe, Daniel B. Dougherty, and Marc Ulrich . . . . .	051804
<b>Stiction-free fabrication of lithographic nanostructures on resist-supported nanomechanical resonators</b>	
Zhu Diao, Joseph E. Losby, Jacob A. J. Burgess, Vincent T. K. Sauer, Wayne K. Hiebert, and Mark R. Freeman . . . . .	051805

### Microelectronic & Nanoelectronic Devices

<b>GaN metal–insulator–semiconductor high-electron-mobility transistor with plasma enhanced atomic layer deposited AlN as gate dielectric and passivation</b>	
Ya-Hsi Hwang, Lu Liu, Camilo Velez, Fan Ren, Brent P. Gila, David Hays, Stephen J. Pearton, Eric Lambers, Ivan I. Kravchenko, Chien-Fong Lo, and Jerry W. Johnson . . . . .	052201
<b>Influence of Al/TiN/SiO<sub>2</sub> structure on MOS capacitor, Schottky diode, and fin field effect transistors devices</b>	
Lucas P. B. Lima, José A. Diniz, Claudio Radtke, Marcos V. P. dos Santos, Ioshiaki Doi, and José Godoy Fo . . .	052202
<b>Field emission properties of carbon nanotube emitters dependent on electrode geometry</b>	
Yenan Song, Dong Hoon Shin, Seok-Gy Jeon, Jung-Il Kim, and Cheol Jin Lee . . . . .	052203
<b>High current hybrid single walled carbon nanotube/graphene field emitters</b>	
Daniela Leberl, Bernhard Hensel, Heinrich Kapitzka, Heinrich Zeininger, and Sandro F. Tedde . . . . .	052204

### Errata

<b>Erratum: “Resonant coupling for contactless measurement of carrier lifetime” [J. Vac. Sci. Technol. B 31, 04D113 (2013)]</b>	
Richard K. Ahrenkiel . . . . .	053401
<b>CUMULATIVE AUTHOR INDEX . . . . .</b>	<b>A9</b>

**On The Cover:** Igor Levchenko, Michael Keidar, Shuyan Xu, Holger Kersten, and Kostya (Ken) Ostrikov, *JVST B*, **31**(5), p. 050801-1 (2013). Cover shows diverse carbon nanostructures (e.g., fullerenes, nanotubes, graphenes) that can be effectively produced using low-temperature plasmas.